

UC Berkeley

EE C247B - ME C218 Introduction to MEMS Design Fall 2016

Prof. Clark T.-C. Nguyen

Dept. of Electrical Engineering & Computer Sciences
 University of California at Berkeley
 Berkeley, CA 94720

Module 17: Noise & MDS

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 1

UC Berkeley

Lecture Outline

- Reading: Senturia Chpt. 16
- Lecture Topics:
 - ↳ Minimum Detectable Signal
 - ↳ Noise
 - ↳ Circuit Noise Calculations
 - ↳ Noise Sources
 - ↳ Equivalent Input-Referred Noise
 - ↳ Gyro MDS
 - ↳ Equivalent Noise Circuit
 - ↳ Example ARW Determination

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 2

UC Berkeley

Determining Sensor Resolution

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 3

UC Berkeley

Minimum Detectable Signal (MDS)

- **Minimum Detectable Signal (MDS):** Input signal level when the signal-to-noise ratio (SNR) is equal to unity

```

    graph LR
        S((Sensed Signal)) --> Sensor
        subgraph Sensor
            SFS[Sensor Scale Factor]
            SN[Sensor Noise]
            SFS --> Sum1((+))
            SN --> Sum1
        end
        Sum1 --> SCC[Signal Conditioning Circuit]
        subgraph SCC
            CG[Circuit Gain]
            CON[Circuit Output Noise]
            CG --> Sum2((+))
            CON --> Sum2
        end
        Sum2 --> O((Output))
        O --- Note[Includes desired output plus noise]
    
```

- The sensor scale factor is governed by the sensor type
- The effect of noise is best determined via analysis of the equivalent circuit for the system

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 4

UC Berkeley

Noise

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 5

UC Berkeley

Noise

- **Noise:** Random fluctuation of a given parameter $I(t)$
- In addition, a noise waveform has a zero average value

Avg. value (e.g. could be DC current) I_D

- We can't handle noise at instantaneous times
- But we can handle some of the averaged effects of random fluctuations by giving noise a power spectral density representation
- Thus, represent noise by its mean-square value:

Let $i(t) = I(t) - I_D$

Then $\overline{i^2} = \overline{(I - I_D)^2} = \lim_{T \rightarrow \infty} \frac{1}{T} \int_0^T |I - I_D|^2 dt$

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 6

UC Berkeley

Noise Spectral Density

- We can plot the spectral density of this mean-square value:

$\frac{\overline{i^2}}{\Delta f}$ [units²/Hz]

One-sided spectral density
→ used in circuits
→ measured by spectrum analyzers

Two-sided spectral density (1/2 the one-sided)

Often used in systems courses

$\overline{i^2}$ = integrated mean-square noise spectral density over all frequencies (area under the curve)

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 7

UC Berkeley

Circuit Noise Calculations

Deterministic

Inputs $v_i(j\omega)$

Outputs $v_o(j\omega)$

Linear Time-Invariant System $H(j\omega)$

Random

Mean square spectral density $S_o(\omega)$

No j -noise near random phase, so j is pointless!

- **Deterministic:** $v_o(j\omega) = H(j\omega)v_i(j\omega)$
- **Random:** $S_o(\omega) = [H(j\omega)H^*(j\omega)]S_i(\omega) = |H(j\omega)|^2 S_i(\omega)$

$\sqrt{S_o(\omega)} = |H(j\omega)| \sqrt{S_i(\omega)}$ → How is it we can do this?

Root mean square amplitudes

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 8

Handling Noise Deterministically

Can do this for noise in a tiny bandwidth (e.g., 1 Hz)

Can approximate this by a sinusoidal voltage generator (especially for small B, say 1 Hz)

[This is actually the principle by which oscillators work → oscillators are just noise going through a tiny bandwidth filter]

Why? Neither the amplitude nor the phase of a signal can change appreciably within a time period $1/B$.

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 9

Systematic Noise Calculation Procedure

General Circuit With Several Noise Sources

- Assume noise sources are uncorrelated
- 1. For i_{n1}^2 , replace w/ a deterministic source of value

$$i_{n1} = \sqrt{\frac{i_{n1}^2}{\Delta f}} \cdot (1 \text{ Hz})$$

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 10

Systematic Noise Calculation Procedure

- Calculate $v_{on1}(\omega) = i_{n1}(\omega)H(j\omega)$ (treating it like a deterministic signal)
- Determine $v_{on1}^2 = i_{n1}^2 \cdot |H(j\omega)|^2$
- Repeat for each noise source: $i_{n1}^2, v_{n2}^2, v_{n3}^2$
- Add noise power (mean square values)

$$v_{onTOT}^2 = v_{on1}^2 + v_{on2}^2 + v_{on3}^2 + v_{on4}^2 + \dots$$

$$v_{onTOT} = \sqrt{v_{on1}^2 + v_{on2}^2 + v_{on3}^2 + v_{on4}^2 + \dots}$$

Total rms value

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 11

Noise Sources

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 12

Thermal Noise

- Thermal Noise in Electronics:** (Johnson noise, Nyquist noise)
 - Produced as a result of the thermally excited random motion of free e⁻s in a conducting medium
 - Path of e⁻s randomly oriented due to collisions
- Thermal Noise in Mechanics:** (Brownian motion noise)
 - Thermal noise is associated with all dissipative processes that couple to the thermal domain
 - Any damping generates thermal noise, including gas damping, internal losses, etc.
- Properties:**
 - Thermal noise is white (i.e., constant w/ frequency)
 - Proportional to temperature
 - Not associated with current
 - Present in any real physical resistor

EE247B/ME218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 13

Circuit Representation of Thermal Noise

- Thermal Noise can be shown to be represented by a series voltage generator $\overline{v_R^2}$ or a shunt current generator $\overline{i_R^2}$

$\frac{\overline{i_R^2}}{\Delta f} = \frac{4kT}{R}$

$\frac{\overline{v_R^2}}{\Delta f} = 4kTR$

Note: These are one-sided mean-square spectral densities! To make them 2-sided, must divide by 2. where $4kT = 1.66 \times 10^{-20} V \cdot C$ and where these are spectral densities.

EE247B/ME218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 14

Noise in Capacitors and Inductors?

- Resistors generate thermal noise
- Capacitors and inductors are noiseless → why?

- Now, add a resistor:
 - Decays to zero
 - But this violates the laws of thermodynamics, which require that things be in constant motion at finite temperature

Need to add a forcing function, like a noise voltage $\overline{v_R^2}$ to keep the motion going → and this noise source is associated with R

EE247B/ME218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 15

Why 4kTR?

- Why is $\overline{v_R^2} = 4kTR\Delta f$ (a heuristic argument)
- The Equipartition Theorem of Statistical Thermodynamics says that there is a mean energy $(1/2)kT$ associated w/ each degree of freedom in a given system
- An electronic circuit possesses two degrees of freedom:
 - Current, i, and voltage, v
 - Thus, we can write:

$$\frac{1}{2}Li^2 = \frac{1}{2}k_B T \quad , \quad \frac{1}{2}Cv^2 = \frac{1}{2}k_B T$$
- Similar expressions can be written for mechanical systems
 - For example: for displacement, x

$$\frac{1}{2}kx^2 = \frac{1}{2}k_B T$$

EE247B/ME218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 16

Why 4kTR? (cont)

UC Berkeley

- Why is $\overline{v_R^2} = 4kTR\Delta f$? (a heuristic argument)
- Consider an RC circuit:

$E = \frac{1}{2} kT \cdot \frac{1}{2} C \overline{v_C^2}$

$\therefore \overline{v_C^2} = \frac{kT}{C}$ ← integrated noise over all freqs.
(total mean square voltage integrated over all freqs.)

Question: What value of $\frac{\overline{v_R^2}}{\Delta f}$ (assuming white noise) gives us this?

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 17

Why 4kTR? (cont)

UC Berkeley

Question: What value of $\frac{\overline{v_R^2}}{\Delta f}$ (assuming white noise) gives us $\overline{v_C^2} = \frac{kT}{C}$?

$\overline{v_C^2} = \int_0^\infty \left| \frac{1}{1+j\omega RC} \right|^2 \frac{\overline{v_R^2}}{\Delta f} d\omega$

[noise is white] $\rightarrow \frac{\overline{v_R^2}}{\Delta f} = \frac{1}{2\pi} \int_0^\infty \frac{\omega_b^2}{\omega_b^2 + \omega^2} d\omega$

[$\omega_b = \frac{1}{RC}$]

$\left[\int \frac{dx}{x^2+a^2} = \frac{1}{a} \tan^{-1}\left(\frac{x}{a}\right) \right]$

$= \frac{1}{2\pi} \frac{\overline{v_R^2}}{\Delta f} \frac{\omega_b^2}{\omega_b} \tan^{-1}\left(\frac{\omega}{\omega_b}\right) \Big|_0^\infty = \frac{1}{2\pi} \frac{\overline{v_R^2}}{\Delta f} \left(\frac{\pi}{2} \omega_b - 0 \right)$

$= \frac{1}{4} \omega_b \frac{\overline{v_R^2}}{\Delta f} = \frac{kT}{C} \rightarrow \frac{\overline{v_R^2}}{\Delta f} = 4kT \left(\frac{\omega_b}{C} \right) \Rightarrow \frac{\overline{v_R^2}}{\Delta f} = 4kTR$ ✓

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 18

Shot Noise

UC Berkeley

- Associated with direct current flow in diodes and bipolar junction transistors
- Arises from the random nature by which e^- 's and h^+ 's surmount the potential barrier at a pn junction
- The DC current in a forward-biased diode is composed of h^+ 's from the p-region and e^- 's from the n-region that have sufficient energy to overcome the potential barrier at the junction
→ noise process should be proportional to DC current
- Attributes:
 - Related to DC current over a barrier
 - Independent of temperature
 - White (i.e., const. w/ frequency)
 - Noise power $\sim I_D$ & bandwidth

pn-junction

$$\frac{i_n^2}{\Delta f} = 2qI_D$$

Charge on an e^- ($=1.6 \times 10^{-19} C$)

DC Current

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 19

Flicker (1/f) Noise

UC Berkeley

- In general, associated w/ random trapping & release of carriers from "slow" states
- Time constant associated with this process gives rise to a noise signal w/ energy concentrated at low frequencies
- Often, get a mean-square noise spectral density that looks like this:

$$\frac{i_n^2}{\Delta f} = 2qI_D + K \left(\frac{I_D^a}{f^b} \right)$$

I_D = DC current
 K = const. for a particular device
 $a = 0.5 \rightarrow 2$
 $b \sim 1$

1/f Noise Corner Frequency

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 20

Example: Typical Noise Numbers

• Hookup the circuit below and make some measurements

Measure w/ AC voltmeter
Measure w/ spectrum analyzer
Get Gaussian amplitude distribution

Low Noise Amplifier
100x

Probability

area $\sim n^2$

$4kTR$

$2\pi RC$

$1k\Omega: 4nV/\sqrt{Hz}$ (for every 1k of R)
 $1pF: \sqrt{\frac{kT}{C}} = 64\mu V \text{ rms}$

68% within $\pm\sigma$
99.7% within $\pm 3\sigma$

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 21

Example: Typical Noise Numbers

• Hookup the circuit below and make some measurements

Measure w/ AC voltmeter
Measure w/ spectrum analyzer

Low Noise Amplifier
100x

AC Voltmeter
 $\sqrt{N_b^2} = (100)(64\mu V \text{ rms}) = 6.4 \text{ mV rms}$

Spectrum Analyzer
 $(2\pi)(1k)(1p) = 60 \text{ MHz}$
 $400 \text{ nV}/\sqrt{Hz}$
20 dB/dec
one-sided spectral density

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 22

Back to Determining Sensor Resolution

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 23

MEMS-Based Tuning Fork Gyroscope

Sense Electrodes
Tuning Electrodes
Drive Electrode
Drive
Sense
Sense Electrodes

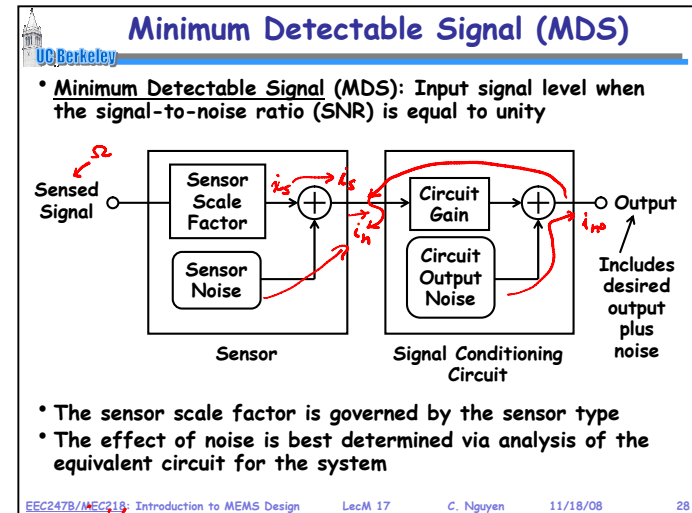
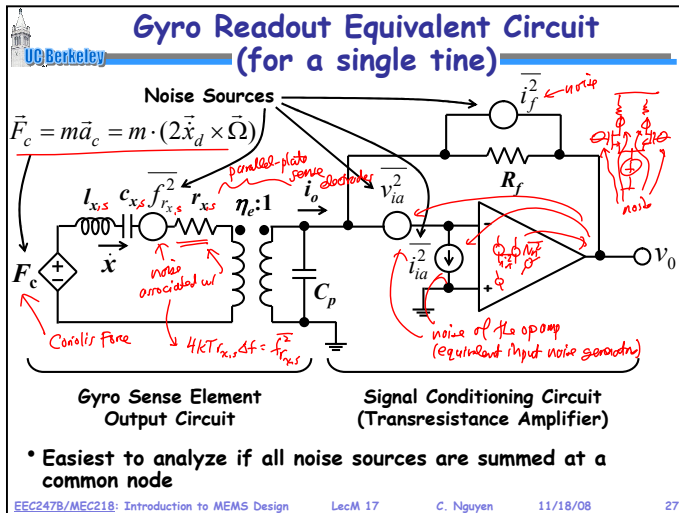
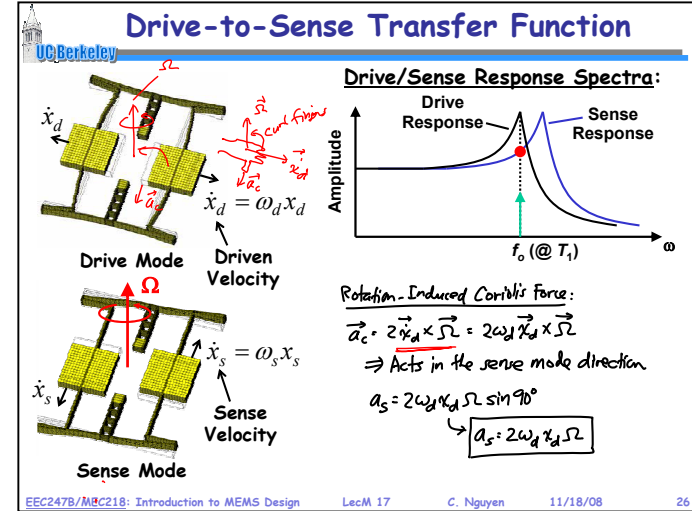
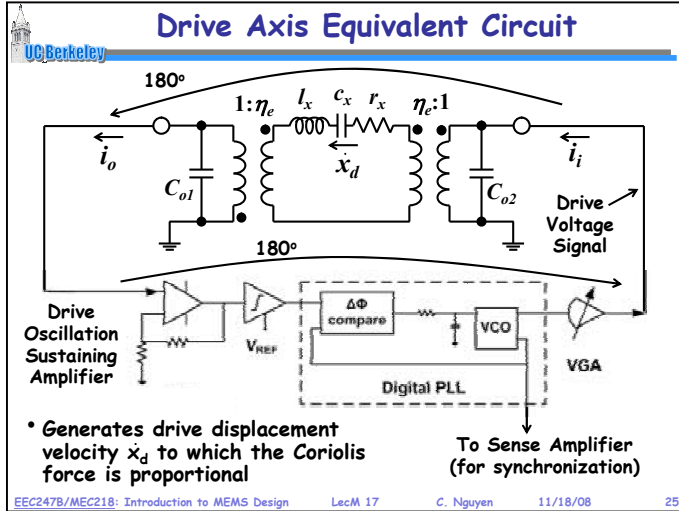
Drive Voltage Signal

(-) Sense Output Current
(+) Sense Output Current

Drive Oscillation Sustaining Amplifier
Differential TransR Sense Amplifier

[Zaman, Ayazi, et al, MEMS'06]

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 24



Move Noise Sources to a Common Point

- Move noise sources so that all sum at the input to the amplifier circuit (i.e., at the output of the sense element)
- Then, can compare the output of the sensed signal directly to the noise at this node to get the MDS

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 29

Equivalent Input-Referred Voltage and Current Noise Sources

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 30

Equivalent Input v, i Noise Generators

- Take a noisy 2-port network and represent it by a noiseless network with input v and i noise generators that generate the same total output noise

- **Remarks:**
 1. Works for linear time-invariant networks
 2. v_{eq} and i_{eq} are generally correlated (since they are derived from the same sources)
 3. In many practical circuits, one of v_{eq} and i_{eq} dominates, which removes the need to address correlation
 4. If correlation is important \rightarrow easier to return to original network with internal noise sources

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 31

Calculation of v_{eq}^2 and i_{eq}^2

a) To get $\overline{v_{eq}^2}$ for a two-port:

Case I

Case II

- 1) Short input, find $\overline{v_{0I}^2}$ (or $\overline{i_{0I}^2}$)
- 2) For eq. network, short input, find $\overline{v_{0II}^2}$ (or $\overline{i_{0II}^2}$)

$$\overline{v_{eq}^2} = \overline{v_{0II}^2} \cdot f(v_{eq}^2) \quad \overline{i_{eq}^2} = \overline{i_{0II}^2} \cdot f(i_{eq}^2)$$

- 3) Set $\overline{v_{0I}^2} = \overline{v_{0II}^2} \rightarrow$ solve for $\overline{v_{eq}^2}$ (or $\overline{i_{0I}^2} = \overline{i_{0II}^2}$)

EEC247B/MEC218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 32

Calculation of v_{eq}^2 and i_{eq}^2 (cont)

b) To get i_{eq}^2 for a 2-port:

- 1) Open input, find v_{0I}^2 (or i_{0I}^2)
- 2) Open input for eq. circuit, find v_{0II}^2 (or i_{0II}^2)
- 3) Set $v_{0I}^2 = v_{0II}^2$ (or $i_{0I}^2 = i_{0II}^2$) → solve for i_{eq}^2 (or $v_{eq}^2 = v_{0II}^2$)

• Once the equivalent input-referred noise generators are found, noise calculations become straightforward as long as the noise generators can be treated as uncorrelated

EEC247B/ME218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 33

Cases Where Correlation Is Not Important

- There are two common cases where correlation can be ignored:
 1. Source resistance R_s is **small** compared to input resistance R_i → i.e., voltage source input
 2. Source resistance R_s is **large** compared to input resistance R_i → i.e., current source input

1) $R_s = \text{small}$ (ideally = 0 for an ideal voltage source):

∴ For $R_s = \text{small}$, i_{eq}^2 can be neglected → only v_{eq}^2 is important!
(Thus, we need not deal with correlation)

EEC247B/ME218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 34

Cases Where Correlation Is Not Important

2) $R_s = \text{large}$ (Ideally = ∞ for an ideal current source)

∴ For $R_s = \text{large}$, v_{eq}^2 can be neglected!
→ only i_{eq}^2 is important!
(... and again, we need not deal with correlation)

EEC247B/ME218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 35

Example: TransR Amplifier Noise

Input-referred current noise:

Open input; equate output voltage noise.

Case I:

$$N_{0II} = i_{ia} R_f$$

$$N_{0I2} = i_f R_f$$

$$N_{0I3} = N_{ia}$$

More N_{ia} through R_{in} to N_{ia} . This is unity gain!

$$\therefore N_{0I2}^2 = i_{ia}^2 R_f^2 + i_f^2 R_f^2 + N_{ia}^2$$

Case II:

$$N_{0II}^2 = i_{eq}^2 R_f^2$$

$$\therefore i_{eq}^2 = i_{ia}^2 + i_f^2 + \frac{N_{ia}^2}{R_f^2}$$

EEC247B/ME218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 36

Example: TransR Amplifier Noise (cont)

UC Berkeley

Input-referred voltage noise:
 Short inputs; equate output voltage noise

Case I:
 $\overline{N_{oI}}^2 = \overline{N_{ia}}^2 a^2$
 (Both $\overline{N_{ia}}^2$ & $\overline{N_f}^2$ are shorted out.)

Case II:
 $\overline{N_{oII}}^2 = \overline{N_{eq}}^2 a^2$
 $\therefore \overline{N_{eq}}^2 = \overline{N_{ia}}^2$

EEC247B/ME218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 37

Example: TransR Amplifier Noise (cont)

UC Berkeley

- To summarize, for a transresistance amplifier, the equivalent input-referred current and voltage noise generators are given by:

$$\overline{i_{eq}}^2 = \overline{i_{ia}}^2 + \overline{i_f}^2 + \frac{\overline{v_{ia}}^2}{R_f^2}$$

$$\overline{v_{eq}}^2 = \overline{v_{ia}}^2$$

EEC247B/ME218: Introduction to MEMS Design LecM 17 C. Nguyen 11/18/08 38